

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	10/591581.app.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 07:59
S3	129	"111" near2 twins and ("257" "438").clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 09:42
S2	371	"111" near2 twins	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 09:42
S6	5	("257" "438").clas. and "111" near2 twins same boron near5 phosphide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 09:43
S5	0	("257" "438").clas. and "111" near2 twins same boron near5 phosphate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 09:43
S4	0	("257" "438").clas. and "111" near2 twins same boron near5 phsphate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 09:43
S7	12	("257" "438").clas. and "111" near2 twins and boron near5 phosphide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 09:45

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S8	3	("257" "438").clas. and lattice near5 (mis near1 match\$5 mismatch\$5 match\$5) near5 twins and boron near5 phosphide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 18:42
S9	10	("257" "438").clas. and lattice near5 (mis near1 match\$5 mismatch\$5 match\$5) near5 twins	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 18:43
S11	13	("257" "438").clas. and lattice near5 (mis near1 match\$5 mismatch\$5 match\$5) near5 twin\$6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 18:44
S10	13	("257" "438").clas. and lattice near5 (mis near1 match\$5 mismatch\$5 match\$5) near5 twin\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 18:44
S12	44	("257" "438").clas. and lattice near5 (mis near1 match\$5 mismatch\$5 match\$5) same form\$3 same twin\$6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 18:50
S13	5	lattice near5 (mis near1 match\$5 mismatch\$5 match\$5) near5 twin\$5 and boron near5 phosphide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 18:54
S14	2	"20030160253".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 19:00

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S16	12	"2111" near2 direction and ("257" "438"). clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 19:09
S15	69	"2111" near2 direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 19:09
S17	4	"2110" near2 direction and ("257" "438"). clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 19:10
S19	6	[-2110] near2 direction and ("257" "438"). clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 19:12
S18	131	"2110" near2 direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/07 19:12
S20	10	[-2110] near5 (boundary direction) and ("257" "438").clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/09 08:15
S22	5	("257" "438").clas. and (hexagonal) near10 againn same cubic near10 againn	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/09 09:40

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S23	3	boron near1 phosphide near5 crystal near2 lattice near5 cubic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:01
S24	7	boron near1 phosphide same crystal near2 lattice near5 cubic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:12
S26	11	("257" "372" "438").clas. and twin\$4 near5 dislocation same (boron near1 phosphide BP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:19
S25	172	"257".clas. and twin\$4 near5 dislocation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:19
S28	11	("257" "372" "438").clas. and twin\$5 near5 dislocation and (boron near1 phosphide BP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:22
S27	11	("257" "372" "438").clas. and twin\$4 near5 dislocation and (boron near1 phosphide BP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:22
S29	19	("257" "372" "438").clas. and (light near1 emi\$5 near1 (element device diode) (bh dh diode semiconductor) near1 laser) and twin\$5 near5 dislocation and (phosphide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:26

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S30	23	("257" "438" "372").clas. and twin\$4 same (strain stress lattice near2 mismatch\$4) near5 (relief reliev\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:29
S31	2	"7646040".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 09:35
S32	8	(cubic same (zinc near1 blend zincblend)) same (bp boron near1 phosphide boronphosphide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 11:22
S33	559	(cubic (zinc near1 blend zincblend)) same (bp boron near1 phosphide boronphosphide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 11:26
S35	68	("257" "372" "438").clas. and (cubic (zinc near1 blend zincblend)) same (bp boron near1 phosphide boronphosphide) and (dislocation twin\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 11:27
S34	14	("257" "372" "438").clas. and (cubic (zinc near1 blend zincblend)) same (bp boron near1 phosphide boronphosphide) and twin\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 11:27
S36	56	("257" "372" "438").clas. and (light near1 emi\$5 near1 (diode device) (BH DH semiconductor diode) near1 laser) and (cubic (zinc near1 blend zincblend)) same (bp boron near1 phosphide boronphosphide) and (dislocation twin\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 11:28

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S37	1	("257" "372" "438").clas. and "-2110" same "110"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 12:24
S40	1	"[-2110]" and "[110]"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 12:27
S39	1	("257" "372" "438").clas. and "[-2110]" and "[110]"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 12:27
S38	1	("257" "372" "438").clas. and "[-2110]" same "[110]"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 12:27
S41	18	("257" "372" "438").clas. and "[-2110]"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 12:28
S42	156	("257" "372" "438").clas. and "[110]" near10 direction near10 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:09
S44	0	("257" "372" "438").clas. and "[110]" near10 direction near10 layer same c near1 direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:15

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S43	0	("257" "372" "438").clas. and "[110]" near10 direction near10 layer same c near1 plane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:15
S45	2	("257" "372" "438").clas. and "[110]" near10 direction near10 layer same c near2 surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:16
S46	88177	("257" "372" "438").clas. and "[-2110] [1-210] [11-20] [110-21]" near10 direction near10 layer relax	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:18
S47	0	("257" "372" "438").clas. and "[-2110] [1-210] [11-20] [110-21]" near10 direction near10 layer near10 relax\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:19
S48	0	("257" "372" "438").clas. and ([11-20] [1210] [-2110] [-1-120] [-12-10] [2-1-10]) near10 direction near10 layer near10 relax\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:20
S49	4	("257" "372" "438").clas. and ([11-20] [1210] [-2110] [-1-120] [-12-10] [2-1-10]) same relax\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:21
S50	105	("257" "372" "438").clas. and ([11-20] [1210] [-2110] [-1-120] [-12-10] [2-1-10]) same gan	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:24

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S51	16	(US-20030160253-\$ or US-20030027099-\$ or US-20030047795-\$ or US-20070267722-\$ or US-20010036678-\$ or US-20040232404-\$ or US-20050121693-\$ or US-20020000563-\$ or US-20010054717-\$).did. or (US-3877060-\$ or US-7646040-\$ or US-7315050-\$ or US-6831304-\$ or US-6737678-\$ or US-3962716-\$ or US-6254675-\$).did.	US-PGPUB; USPAT	OR	ON	2010/06/06 14:08
S52	128	(257/12,13,79,94,97,103,201,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide)	US-PGPUB; USPAT	OR	ON	2010/06/06 14:26
S53	82	(257/12,13,79,94,97,103,201,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and silicon near10 substrate	US-PGPUB; USPAT	OR	ON	2010/06/06 14:27
S54	65	(257/12,13,79,94,97,103,201,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and silicon near10 substrate and clad\$5	US-PGPUB; USPAT	OR	ON	2010/06/06 15:16
S55	47	(257/12,13,79,94,97,103,201,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) same clad\$5 and silicon near10 substrate	US-PGPUB; USPAT	OR	ON	2010/06/06 15:17
S56	2	10/332200.app.	US-PGPUB; USPAT	OR	ON	2010/06/06 15:29
S57	25	undoped near10 p-type near10 bp	US-PGPUB; USPAT	OR	ON	2010/06/06 15:47
S58	30	undoped near10 n-type near10 bp	US-PGPUB; USPAT	OR	ON	2010/06/06 15:49
S59	7	misfit near1 dislocation near5 twin	US-PGPUB; USPAT	OR	ON	2010/06/06 16:12
S60	74	(257/12,13,79,94,97,103,201,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and silicon near10 substrate and n near1 type and p near1 type	US-PGPUB; USPAT	OR	ON	2010/06/06 16:21
S61	74	(257/12,13,79,94,97,103,201,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and silicon near10 substrate and n near1 type and p near1 type	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 16:22

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S63	6	S62 not S61	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 16:37
S62	80	(257/12,13,79,94,97,103,201,e33.003,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and silicon near10 substrate and n near1 type and p near1 type	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 16:37
S64	23	(257/12,13,79,94,97,103,201,e33.003,e33.013,e33.025 438/47).ccls. and ((bp boron near1 phosphide boronphosphide) and silicon near10 substrate).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 16:39
S65	5	(257/12,13,79,94,97,103,201,e33.003,e33.013,e33.025 438/47).ccls. and ((bp boron near1 phosphide boronphosphide) and silicon near10 substrate and twin\$5).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 16:40
S66	64	(udagawa and takashi).in. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and silicon near10 substrate and n near1 type and p near1 type	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/06 17:09
S67	15	(udagawa and takashi).in. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and silicon near10 substrate and n near1 type and p near1 type and twin\$5	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/06 17:10
S68	17	hexagonal near10 boron near1 phosphide	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/06 17:19
S69	47	(bp boronphosphide boron near1 phosphide) and twin\$5 same (strain stress lattice near1 mismatch\$3) same (reliev\$5 relief reduc\$4 decreas\$5)	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/06 17:25
S70	52	(bp boronphosphide boron near1 phosphide) and twin\$5 same (strain stress lattice near1 mismatch\$3) same (reliev\$5 relief reduc\$4 decreas\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 17:26

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S71	4	"2003065465"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 17:39
S72	0	crystal near2 lattice near2 gan near2 hex\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 18:58
S73	46	crystal near2 structure near2 gan near2 hexagonal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 18:59
S74	2	"10502597"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 19:45
S75	28	phosphorus near5 concentration near15 adhesion	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/22 09:00
S76	304	boron with phosphide with gap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/18 12:43
S79	45	boron near10 phosphide near10 based with (bandgap band near1 gap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/18 12:44

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S78	79	boron near10 phosphide with (bandgap band near1 gap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/18 12:44
S77	264	boron near10 phosphide with gap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/18 12:44
S80	7	boron near10 phosphide near10 based same lattice same (bandgap band near1 gap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/18 13:41
S81	21	boron near10 phosphide near10 based same lattice near10 match\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/18 13:44
S82	35	dopant near5 (density concentration) near20 active near2 (layer region film) near50 (recombination gneration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 13:04
S83	44	dopant near5 (density concentration) near30 active near2 (layer region film) near50 (recombination generation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 13:32
S85	12	dopant near5 (density concentration) near30 active near2 (layer region film) near50 (increas\$4) near5 (conductivity)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 13:51

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S84	245	dopant near5 (density concentration) near30 active near2 (layer region film) near50 (conductivity)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 13:51
S86	26	dopant near5 (density concentration) near30 active near2 (layer region film) near50 ((reduc\$5 lower\$4 decreas\$5) near2 resist\$5 (increas\$4) near5 (conduct\$5))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 13:55
S87	135	dopant near5 (density concentration) same active near2 (layer region film) same ((reduc\$5 lower\$4 decreas\$5) near2 resist\$5 (increas\$4) near5 (conduct\$5))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 13:58
S88	467	dop\$4 near5 active near2 (layer region film) same ((reduc\$5 lower\$4 decreas\$5) near2 resist\$4 (increas\$4) near5 (conduct\$5))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 14:01
S90	2	dop\$4 near5 active near2 (layer region film) near20 ((reduc\$5 lower\$4 decreas\$5) near2 resist\$4 (increas\$4) near5 (conduct\$5)) same (led light near1 emi\$5 near1 (device diode laser element))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 14:02
S89	122	dop\$4 near5 active near2 (layer region film) near20 ((reduc\$5 lower\$4 decreas\$5) near2 resist\$4 (increas\$4) near5 (conduct\$5))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 14:02
S91	23	dop\$4 near5 active near2 (layer region film) near20 ((reduc\$5 lower\$4 decreas\$5) near2 resist\$4 (increas\$4) near5 (conduct\$5)) and (light near1 emi\$5 near1 (device diode laser element))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/29 14:04

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S92	55	boron near1 phosphide with lattice near2 constant	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 11:19
S93	28	nitride with boron near1 phosphide with lattice near2 constant	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 12:01
S94	253	(gainn ingan) near5 lattice near1 constant	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 12:27
S95	9	(gainn ingan) near5 lattice near1 constant with shows	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 12:43
S96	3	(gainn ingan) near5 lattice near1 constant with function	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 12:45
S97	8	("Ga.sub.0.90In.sub.0.10N") near5 lattice near1 constant	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 12:58
S98	57	phosphorus near5 dopant near5 (concentration density) near5 diffus\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 13:22

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S99	2	phosphorus near5 dopant near5 (concentration density) near5 diffus\$4 with temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 13:24
S10 0	1	phosphorus near5 dopant near5 (concentration density) near5 diffus\$4 same temperature same nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 13:25
S10 1	26	phosphorus near5 dopant near5 (concentration density) near5 diffus\$4 and temperature and nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 13:26
S10 2	77	phosphorus near10 dopant near10 (concentration density) near10 diffus\$4 and temperature and nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 13:38
S10 3	51	S102 not S101	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/05/02 13:39
S10 4	67	(p phosphorus) near5 concentration near15 adhesion	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/06/02 16:05
S10 5	8	(257/12,13,79,94,97,103,201,e33.003,e33. 013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and silicon near10 substrate and n near1 type and p near1 type and @pd>="20100606"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/06/02 16:44

EAST Search History (Prior Art)

S106	75	(257/12,13,79,94,97,103,201,e33.003,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and (well mqw) and (phosphorus p) near10 concentration	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/06/02 17:23
S107	1	(257/12,13,79,94,97,103,201,e33.003,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and (well mqw) and (phosphorus p) near10 concentration same adhesion	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/06/02 17:25
L2	1	(257/12,13,79,94,97,103,201,e33.003,e33.013,e33.025 438/47).ccls. and (light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and (well mqw) and (phosphorus p) near10 concentration and @pd>="20110602"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/06/09 07:54

EAST Search History (I nterference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S108	3	(257/12,13,79,94,97,103,201,e33.003,e33.013,e33.025 438/47).ccls. and ((light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and (well mqw)).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2011/06/02 17:15
L3	0	(257/12,13,79,94,97,103,201,e33.003,e33.013,e33.025 438/47).ccls. and ((light near1 emi\$5 near1 (device diode)) and (bp boron near1 phosphide boronphosphide) and (well mqw)).clm. and @pd>="20110602"	US-PGPUB; USPAT; UPAD	OR	ON	2011/06/09 08:16